

Abstract**Method for fabricating a semiconductor structure**

The present invention provides a method for fabricating a semiconductor structure having a plurality of gate stacks (GS1, GS2, GS3, GS4) on a semiconductor substrate (10), having the following steps: application of the gate stacks (GS1, GS2, GS3, GS4) to a gate dielectric (11) above the semiconductor substrate (10); formation of a sidewall oxide (17) on sidewalls of the gate stacks (GS1, GS2, GS3, GS4); application and patterning of a mask (12) on the semiconductor structure; and implantation of a contact doping (13) in a self-aligned manner with respect to the sidewall oxide (17) of the gate stacks (GS1, GS2) in regions not covered by the mask (12).

Figure 1B